

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

PMBT3906MB(MS)

Product specification

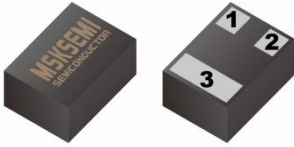
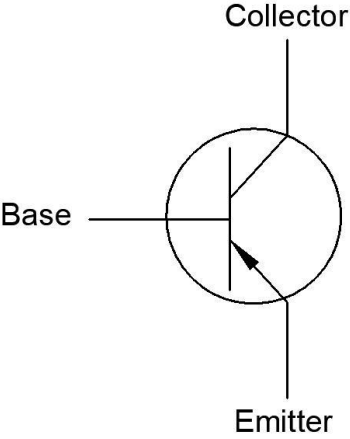

Features

- Low profile package
- Ideal for automated placement
- Complementary to PMBT3904MB(MS) (NPN)
- .Power Dissipation of 200mW
- High Stability and High Reliability
- RoHS Compliant

Applications

- amplifying signal
- Electronic switch
- Oscillating circuit
- variable resistance

Appearance & Symbol

PACKAGE OUTLINE	Pin Configuration	Marking
<div><div>1: Base 2: Emitter 3: Collector</div></div> <div>DFN1006-3</div>	<div><div>Collector</div><div>Base</div><div>Emitter</div></div>	<div></div>

Absolute Maximum Ratings (T=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current - Continuous	I _C	-200	mA
Collector Power Dissipation	P _C	200	mW
Thermal Resistance From Junction to Ambient	R _{θJA}	625	°C/W
Junction Temperature	T _J	-55 to +150	°C
Junction and Storage Temperature	T _{STG}	-55 to +150	°C

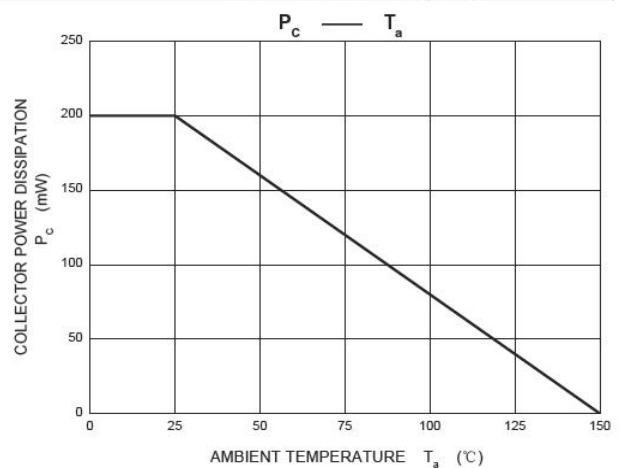
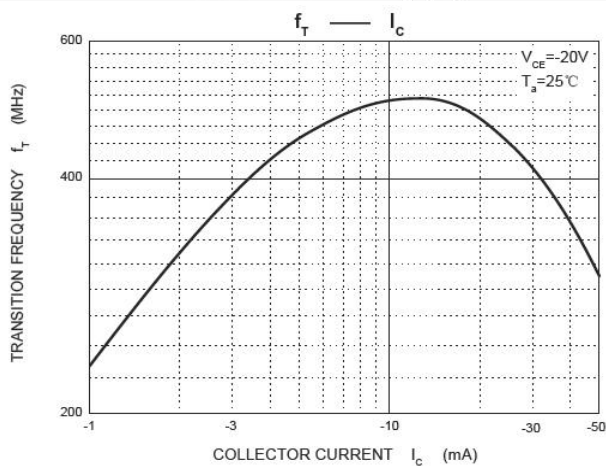
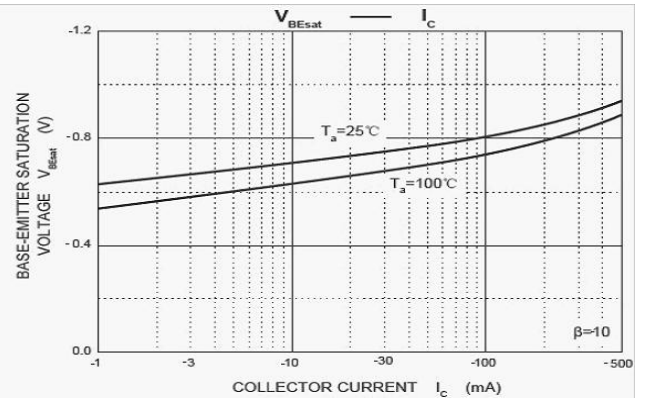
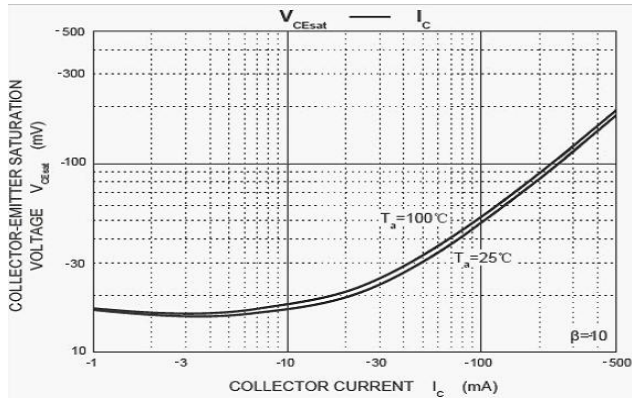
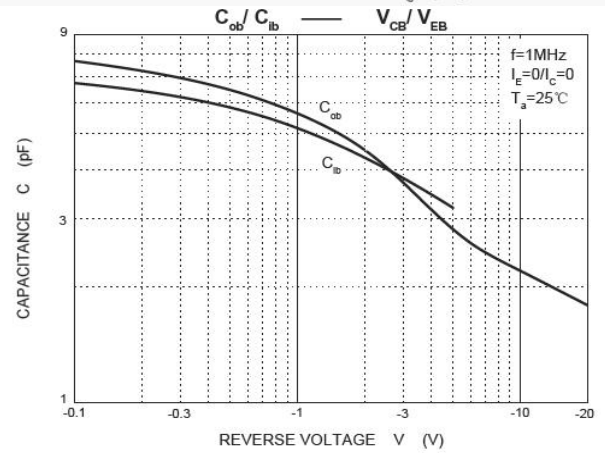
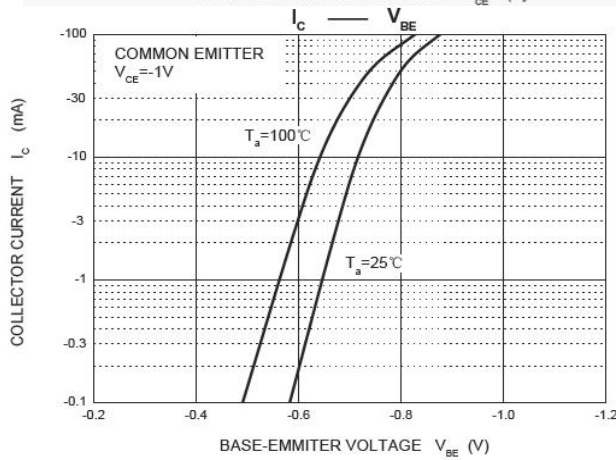
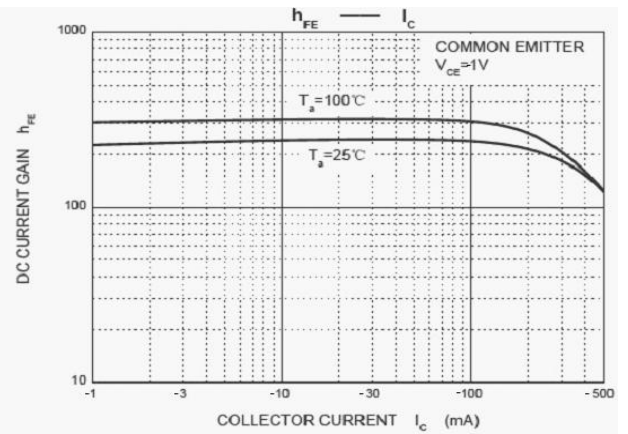
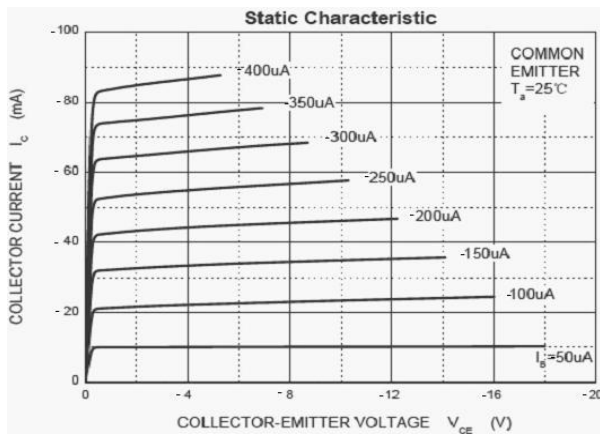
Electrical Characteristics (T=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-40		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-40		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5		V
Collector cut-off current	I _{CEX}	V _{CE} =-30V, V _{BE(Off)} =-3V		-50	nA
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0		-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0		-100	nA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-10mA	100	300	
	h _{FE(2)}	V _{CE} =-1V, I _C =-50mA	60		
	h _{FE(3)}	V _{CE} =-2V, I _C =-100mA	30		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-50mA, I _B =-5mA		-0.3	V
Base -emitter saturation voltage	V _{BE(sat)}	I _C =-50mA, I _B =-5mA		-0.95	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	300		MHz
Delay time	t _d	V _{CC} =-3V, V _{BE} =-0.5V I _C =-10mA, I _{B1} =I _{B2} =-1mA		35	nS
Rise time	t _r			35	nS
Storage time	t _s	V _{CC} =-3V, I _C =-10mA I _{B1} =I _{B2} =-1mA		225	nS
Fall time	t _f			75	nS

Classification of h_{FE}

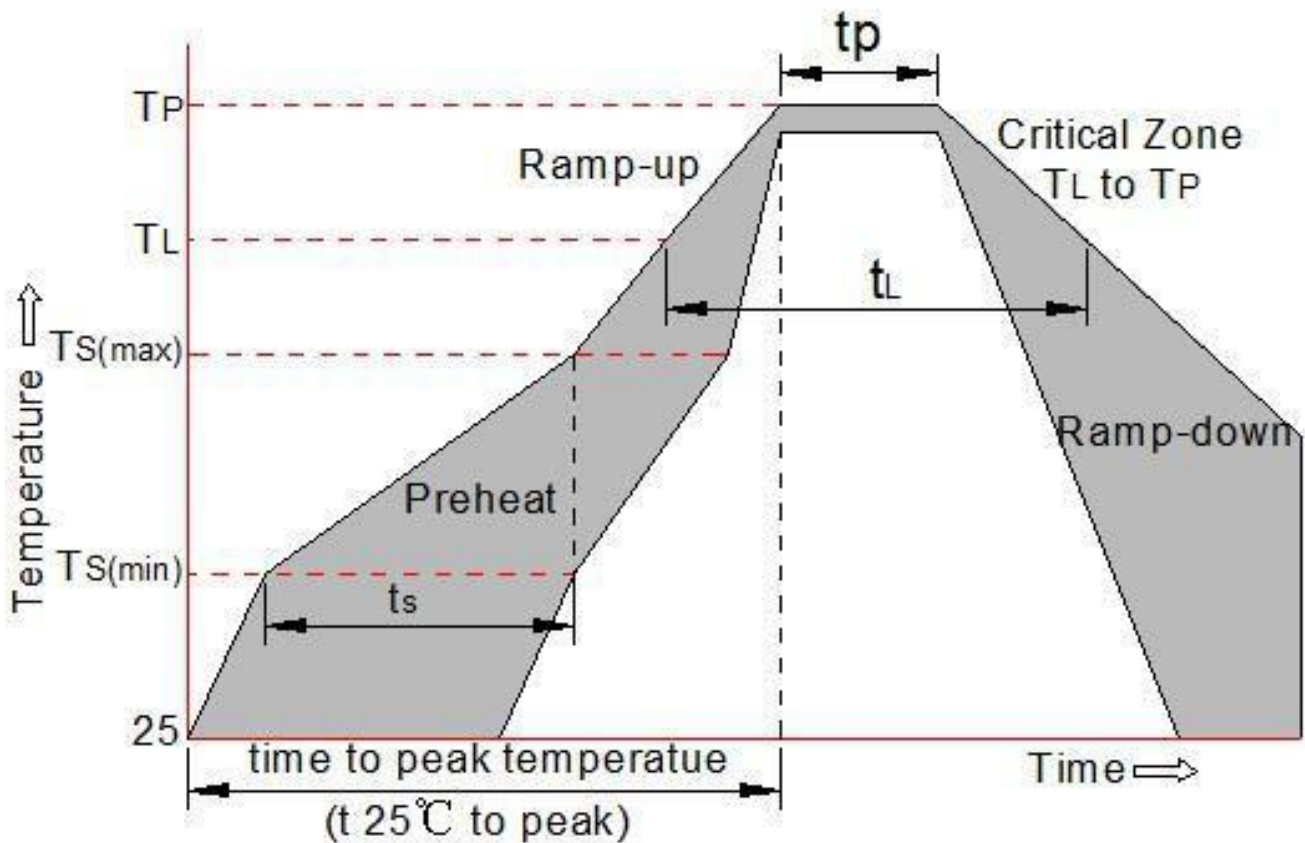
Range	100-300
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Typical Characteristics

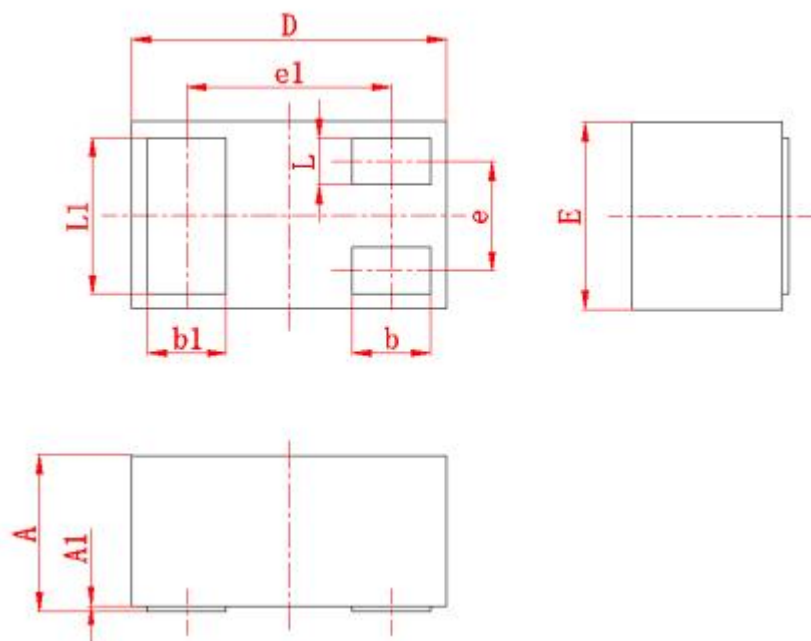


Soldering parameters

Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

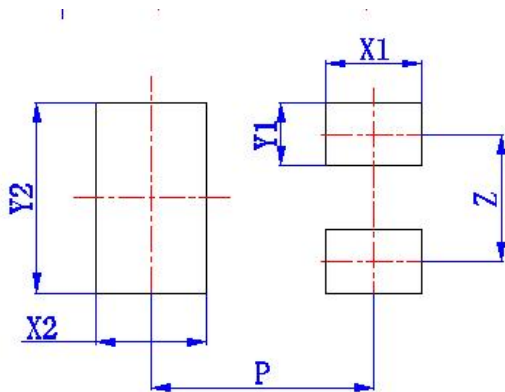


Package mechanical data



Symbol	Millimeters	
	min	max
A	0.4	0.5
A1	0	0.05
D	0.9	1.1
E	0.55	0.65
e	(0.35)	
e1	(0.65)	
b	0.2	0.3
b1	0.2	0.3
L	0.1	0.2
L1	0.45	0.55

Suggested Land Pattern



Symbol	Dimension in Millimeters
	typ
X1	(0.3)
X2	(0.35)
Y1	(0.2)
Y2	(0.6)
Z	(0.4)
P	(0.7)

REEL SPECIFICATION

P/N	PKG	QTY
MMBT3906MB(MS)	DFN1006-3	10000

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